

# 4-Mbit (512K words × 8-bit) Static RAM with Error-Correcting Code (ECC)

### **Features**

- High speed
  - $\Box$   $t_{AA} = 10 \text{ ns}$
- Embedded ECC for single-bit error correction<sup>[1, 2]</sup>
- Low active and standby currents
  - ☐ Active current: I<sub>CC</sub> = 38 mA typical
  - ☐ Standby current: I<sub>SB2</sub> = 6 mA typical
- Operating voltage range: 1.65 V to 2.2 V, 2.2 V to 3.6 V, and 4.5 V to 5.5 V
- 1.0-V data retention
- TTL-compatible inputs and outputs
- Error indication (ERR) pin to indicate 1-bit error detection and correction
- Pb-free 36-pin SOJ and 44-pin TSOP II packages

### **Functional Description**

CY7C1049G and CY7C1049GE are high-performance CMOS fast static RAM devices with embedded ECC. Both devices are offered in single and dual chip-enable options and in multiple pin configurations. The CY7C1049GE device includes an ERR pin that signals an error-detection and correction event during a read cycle.

Data writes are performed by asserting the Chip Enable (CE) and Write Enable (WE) inputs LOW, while providing the data on I/O<sub>0</sub> through I/O<sub>7</sub> and address on A<sub>0</sub> through A<sub>18</sub> pins.

Data reads are performed by asserting the Chip Enable (CE) and Output Enable (OE) inputs LOW and providing the required address on the address lines. Read data is accessible on the I/O lines ( $I/O_0$  through  $I/O_7$ ).

All I/Os (I/O<sub>0</sub> through I/O<sub>7</sub>) are placed in a high-impedance state during the following events:

- The device is deselected (CE HIGH)
- The control signal OE is de-asserted

On the CY7C1049GE devices, the detection and correction of a single-bit error in the accessed location is indicated by the assertion of the ERR output (ERR = HIGH)[1]. See the Truth Table on page 14 for a complete description of read and write

The logic block diagram is on page 2.

### **Product Portfolio**

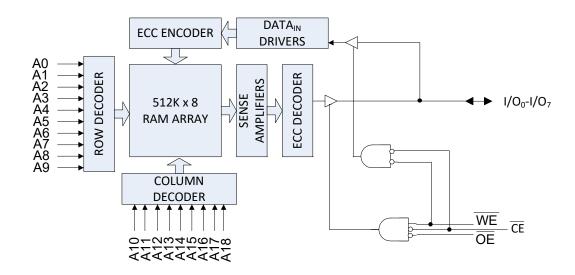
				Power Dissipati			ation	
Product <sup>[3]</sup>	Features and Options (see Pin Configurations on page 4)	Range	V <sub>CC</sub> Range (V)	V <sub>CC</sub> Range (ns)		Operating I <sub>CC</sub> , (mA)		y, I <sub>SB2</sub>
			(V)	10/15	f = f <sub>max</sub>		(m <b>A</b> )	
					<b>Typ</b> <sup>[4]</sup>	Max	<b>Typ</b> <sup>[4]</sup>	Max
CY7C1049G(E)18	Single or Dual Chip Enables	Industrial	1.65 V-2.2 V	15	_	40	6	8
CY7C1049G(E)30	Optional ERR pins		2.2 V-3.6 V	10	38	45		
CY7C1049G(E)	ориона: <u>—</u> . и грию		4.5 V–5.5 V	10	38	45		

- 1. This device does not support automatic write-back on error detection.
- 2. SER FIT Rate < 0.1 FIT/Mb. Refer AN88889 or details.
- 3. The ERR pin is available only for devices which have ERR option "E" in the ordering code. Refer Ordering Information on page 15 for details.
- Typical values are included only for reference and are not guaranteed or tested. Typical values are measured at V<sub>CC</sub> = 1.8 V (for a V<sub>CC</sub> range of 1.65 V-2.2 V),  $V_{CC}$  = 3 V (for a  $V_{CC}$  range of 2.2 V–3.6 V), and  $V_{CC}$  = 5 V (for a  $V_{CC}$  range of 4.5 V–5.5 V),  $T_A$  = 25 °C.

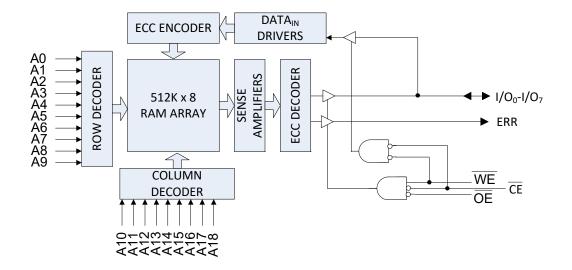
Cypress Semiconductor Corporation Document Number: 001-95412 Rev. \*F



# Logic Block Diagram - CY7C1049G



# Logic Block Diagram - CY7C1049GE





### **Contents**

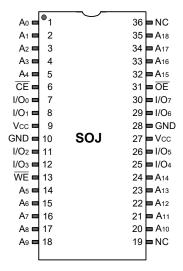
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# **Pin Configurations**

Figure 1. 36-pin SOJ pinout, Single Chip Enable without ERR - CY7C1049G [5]



### Note

5. NC pins are not connected internally to the die.



### Pin Configurations (continued)

Figure 2. 44-pin TSOP II pinout, Single Chip Enable without ERR - CY7C1049G [6]

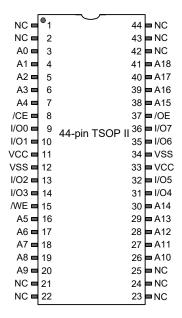
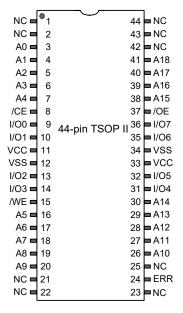


Figure 3. 44-pin TSOP II pinout, Single Chip Enable with ERR - CY7C1049GE [6, 7]



### Notes

- 6. NC pins are not connected internally to the die.
- 7. ERR is an output pin.



# **Maximum Ratings**

Exceeding maximum ratings may impair the useful life of the device. These user guidelines are not tested.

Storage temperature ......-65 °C to +150 °C Ambient temperature Supply voltage 

DC voltage applied to outputs 

DC input voltage [8]	–0.5 V to V <sub>CC</sub> + 0.5 V
Current into outputs (in LOW state)	20 mA
Static discharge voltage (MIL-STD-883, Method 3015)	>2001 V
Latch-up current	> 140 mA

# **Operating Range**

Grade	Ambient Temperature	V <sub>CC</sub>
Industrial	–40 °C to +85 °C	1.65 V to 2.2 V, 2.2 V to 3.6 V, 4.5 V to 5.5 V

### **DC Electrical Characteristics**

Over the operating range of -40 °C to 85 °C

D	Description		Total Consultations	10	ns / 15 i	าร	11!4
Parameter	Desc	ription	Test Conditions	Min	Typ <sup>[9]</sup>	Max	Unit
V <sub>OH</sub>	Output HIGH	1.65 V to 2.2 V	V <sub>CC</sub> = Min, I <sub>OH</sub> = -0.1 mA	1.4	_	_	V
	voltage	2.2 V to 2.7 V	V <sub>CC</sub> = Min, I <sub>OH</sub> = -1.0 mA	2	-	_	
		2.7 V to 3.0 V	V <sub>CC</sub> = Min, I <sub>OH</sub> = -4.0 mA	2.2	-	_	
		3.0 V to 3.6 V	V <sub>CC</sub> = Min, I <sub>OH</sub> = –4.0 mA	2.4	-	_	
		4.5 V to 5.5 V	V <sub>CC</sub> = Min, I <sub>OH</sub> = –4.0 mA	2.4	-	_	
		4.5 V to 5.5 V	V <sub>CC</sub> = Min, I <sub>OH</sub> = -0.1mA	$V_{CC} - 0.5^{[10]}$	-	_	
V <sub>OL</sub>	Output LOW	1.65 V to 2.2 V	V <sub>CC</sub> = Min, I <sub>OL</sub> = 0.1 mA	_	-	0.2	V
	voltage	2.2 V to 2.7 V	V <sub>CC</sub> = Min, I <sub>OL</sub> = 2 mA	_	_	0.4	
		2.7 V to 3.6 V	V <sub>CC</sub> = Min, I <sub>OL</sub> = 8 mA	-	-	0.4	
		4.5 V to 5.5 V	V <sub>CC</sub> = Min, I <sub>OL</sub> = 8 mA	_	_	0.4	
V <sub>IH</sub>	V <sub>IH</sub> Input HIGH voltage	1.65 V to 2.2 V	-	1.4	_	$V_{CC} + 0.2^{[8]}$	V
		2.2 V to 2.7 V	_	2	-	$V_{CC} + 0.3^{[8]}$	
		2.7 V to 3.6 V	-	2	_	$V_{CC} + 0.3^{[8]}$	
		4.5 V to 5.5 V	-	2	_	$V_{CC} + 0.5^{[8]}$	
$V_{IL}$	Input LOW	1.65 V to 2.2 V	_	$-0.2^{[8]}$	-	0.4	V
	voltage	2.2 V to 2.7 V	-	$-0.3^{[8]}$	_	0.6	
		2.7 V to 3.6 V	-	$-0.3^{[8]}$	_	0.8	
		4.5 V to 5.5 V	_	$-0.5^{[8]}$	-	0.8	
I <sub>IX</sub>	Input leakage c	urrent	$GND \le V_{IN} \le V_{CC}$	-1	-	+1	μА
l <sub>OZ</sub>	Output leakage	current	GND ≤ V <sub>OUT</sub> ≤ V <sub>CC</sub> , Output disabled	-1	-	+1	μА
I <sub>CC</sub>	Operating supply current		$Max V_{CC}$ , $I_{QUT} = 0 \text{ mA}$ , $f = 100 \text{ MHz}$	-	38	45	mA
			CMOS levels f = 66.7 MHz	_	_	40	
I <sub>SB1</sub>	Automatic CE power-down current – TTL inputs		$\begin{array}{l} \text{Max V}_{CC}, \overline{CE} \geq V_{IH}, \\ V_{IN} \geq V_{IH} \text{ or } V_{IN} \leq V_{IL},  f = f_{MAX} \end{array}$	_	_	15	mA
I <sub>SB2</sub>	Automatic CE p	ower-down S inputs	Max $V_{CC}$ , $\overline{CE} \ge V_{CC} - 0.2 \text{ V}$ , $V_{IN} \ge V_{CC} - 0.2 \text{ V}$ or $V_{IN} \le 0.2 \text{ V}$ , f = 0	_	6	8	mA

<sup>8.</sup>  $V_{IL(min)}$  = -2.0 V and  $V_{IH(max)}$  =  $V_{CC}$  + 2 V for pulse durations of less than 20 ns.

<sup>9.</sup> Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V<sub>CC</sub> = 1.8 V (for V<sub>CC</sub> range of 1.65 V – 2.2 V),  $V_{CC}$  = 3 V (for  $V_{CC}$  range of 2.2V – 3.6 V), and  $V_{CC}$  = 5 V (for  $V_{CC}$  range of 4.5 V – 5.5 V),  $T_A$  = 25 °C.

<sup>10.</sup> This parameter is guaranteed by design and not tested.



# Capacitance

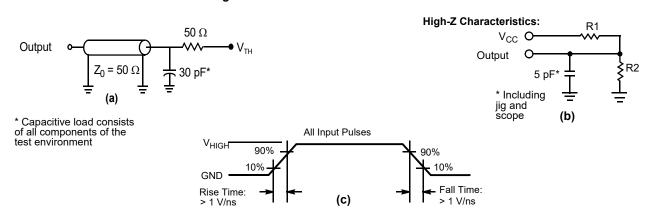
Parameter [11]	Description	on Test Conditions		44-pin TSOP II	Unit
C <sub>IN</sub>	Input capacitance	T <sub>A</sub> = 25 °C, f = 1 MHz,	10	10	pF
C <sub>OUT</sub>	I/O capacitance	$V_{CC} = V_{CC(typ)}$	10	10	pF

### **Thermal Resistance**

Parameter [11]	Description	Test Conditions	36-pin SOJ	44-pin TSOP II	Unit
- JA		Still air, soldered on a 3 × 4.5 inch, four-layer printed circuit board	59.52	68.85	°C/W
- 30	Thermal resistance (junction to case)		31.48	15.97	°C/W

### **AC Test Loads and Waveforms**

Figure 4. AC Test Loads and Waveforms [12]



Parameters	1.8 V	3.0 V	5.0 V	Unit
R1	1667	317	317	Ω
R2	1538	351	351	Ω
V <sub>TH</sub>	0.9	1.5	1.5	V
V <sub>HIGH</sub>	1.8	3	3	V

### Notes

<sup>11.</sup> Tested initially and after any design or process changes that may affect these parameters.

<sup>12.</sup> Full-device AC operation assumes a 100- $\mu$ s ramp time from 0 to  $V_{CC(min)}$  and a 100- $\mu$ s wait time after  $V_{CC}$  stabilization.



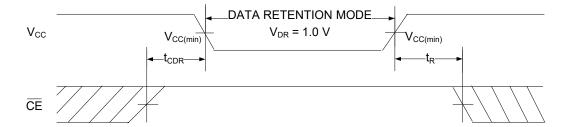
### **Data Retention Characteristics**

Over the operating range of -40 °C to 85 °C

Parameter	Description	Conditions	Min	Max	Unit
$V_{DR}$	V <sub>CC</sub> for data retention		1	_	V
I <sub>CCDR</sub>	Data retention current	$V_{CC} = 1.2 \text{ V}, \overline{CE} \ge V_{CC} - 0.2 \text{ V}^{[14]},$ $V_{IN} \ge V_{CC} - 0.2 \text{ V}, \text{ or } V_{IN} \le 0.2 \text{ V}$	-	8	mA
t <sub>CDR</sub> <sup>[13]</sup>	Chip deselect to data retention time		0	_	ns
t <sub>R</sub> <sup>[13, 14]</sup>	Operation recovery time	V <sub>CC</sub> ≥ 2.2 V	10	_	ns
		V <sub>CC</sub> < 2.2 V	15	_	ns

### **Data Retention Waveform**

Figure 5. Data Retention Waveform<sup>[14]</sup>



<sup>13.</sup> These parameters are guaranteed by design.
14. Full-device operation requires linear V<sub>CC</sub> ramp from V<sub>DR</sub> to V<sub>CC(min)</sub> ≥ 100 μs or stable at V<sub>CC (min)</sub> ≥ 100 μs.



# **AC Switching Characteristics**

Over the operating range of -40 °C to 85 °C

Parameter [15]	Donasistics.	10	ns	15 ns		11.24
Parameter [10]	Description	Min	Max	Min	Max	Unit
Read Cycle		•	•	•		•
t <sub>RC</sub>	Read cycle time	10	_	15	_	ns
t <sub>AA</sub>	Address to data / ERR valid	_	10	_	15	ns
t <sub>OHA</sub>	Data / ERR hold from address change	3	_	3	_	ns
t <sub>ACE</sub>	CE LOW to data / ERR valid	_	10	_	15	ns
t <sub>DOE</sub>	OE LOW to data / ERR valid	_	4.5	_	8	ns
t <sub>LZOE</sub>	OE LOW to low impedance <sup>[16]</sup>	0	_	0	_	ns
t <sub>HZOE</sub>	OE HIGH to HI-Z <sup>[16]</sup>	_	5	_	8	ns
t <sub>LZCE</sub>	CE LOW to low impedance <sup>[16]</sup>	3	_	3	_	ns
t <sub>HZCE</sub>	CE HIGH to HI-Z <sup>[16]</sup>	_	5	_	8	ns
t <sub>PU</sub>	CE LOW to power-up <sup>[17, 18]</sup>	0	_	0	_	ns
t <sub>PD</sub>	CE HIGH to power-down <sup>[17, 18]</sup>	_	10	_	15	ns
Write Cycle [1	8, 19]	•	•	•	1	•
t <sub>WC</sub>	Write cycle time	10	_	15	_	ns
t <sub>SCE</sub>	CE LOW to write end	7	_	12	_	ns
t <sub>AW</sub>	Address setup to write end	7	_	12	_	ns
t <sub>HA</sub>	Address hold from write end	0	_	0	_	ns
t <sub>SA</sub>	Address setup to write start	0	_	0	_	ns
t <sub>PWE</sub>	WE pulse width	7	_	12	_	ns
t <sub>SD</sub>	Data setup to write end	5	-	8	_	ns
t <sub>HD</sub>	Data hold from write end	0	-	0	_	ns
t <sub>LZWE</sub>	WE HIGH to low impedance <sup>[16]</sup>	3	-	3	_	ns
t <sub>HZWE</sub>	WE LOW to HI-Z <sup>[16]</sup>	_	5	_	8	ns

### Notes

<sup>15.</sup> Test conditions assume a signal transition time (rise/fall) of 3 ns or less, timing reference levels of 1.5 V (for  $V_{CC} \ge 3$  V) and  $V_{CC}/2$  (for  $V_{CC} < 3$  V), and input pulse levels of 0 to 3 V (for  $V_{CC} \ge 3$  V) and 0 to  $V_{CC}$  (for  $V_{CC} < 3$  V). Test conditions for the read cycle use output loading, as shown in part (a) of Figure 4 on page 7, unless specified otherwise.

<sup>16.</sup> t<sub>HZOE</sub>, t<sub>HZOE</sub>, t<sub>HZOE</sub>, t<sub>LZOE</sub>, and t<sub>LZWE</sub> are specified with a load capacitance of 5 pF, as shown in part (b) of Figure 4 on page 7. Transition is measured ±200 mV from steady state voltage.

<sup>17.</sup> These parameters are guaranteed by design and are not tested.

<sup>18.</sup> The internal write time of the memory is defined by the overlap of WE = V<sub>IL</sub>, \( \overline{CE} = V\_{IL}.\) These signals must be LOW to initiate a write, and the HIGH transition of any of these signals can terminate the operation. The input data setup and hold timing should be referenced to the edge of the signal that terminates the write.

<sup>19.</sup> The minimum write cycle pulse width in Write Cycle No. 2 (WE Controlled, OE LOW) should be equal to sum of t<sub>DS</sub> and t<sub>HZWE</sub>.



# **Switching Waveforms**

Figure 6. Read Cycle No. 1 of CY7C1049G (Address Transition Controlled)  $^{[20,\,21]}$ 

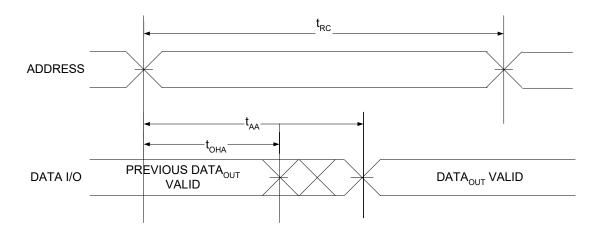
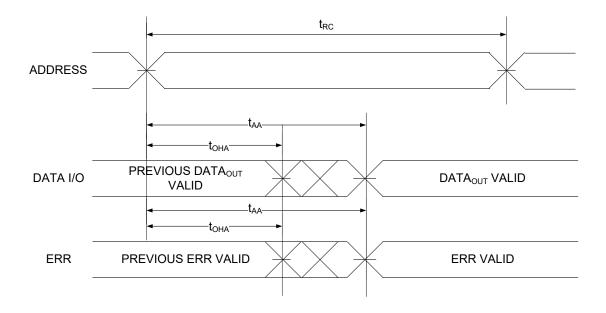


Figure 7. Read Cycle No. 1 of CY7C1049GE (Address Transition Controlled) [20, 21]

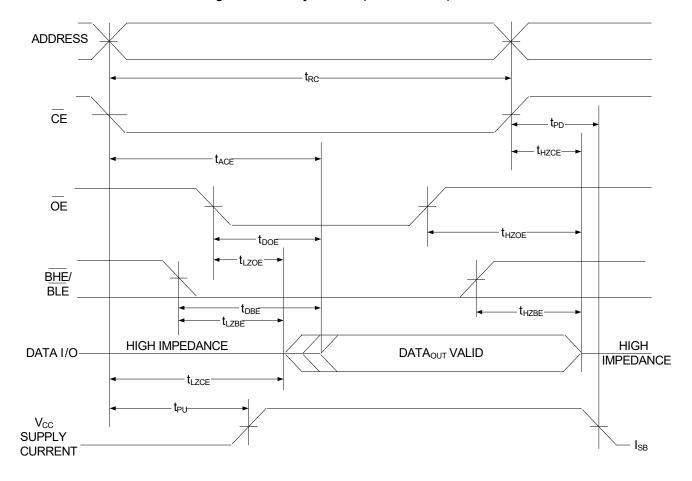


<sup>20.</sup> The device is continuously selected,  $\overline{OE}$  =  $V_{IL}$ ,  $\overline{CE}$  =  $V_{IL}$ . 21.  $\overline{WE}$  is HIGH for the read cycle.



# Switching Waveforms (continued)

Figure 8. Read Cycle No. 2 (OE Controlled) [22, 23]



Notes\_ 22. WE is HIGH for the read cycle.

<sup>23.</sup> Address valid prior to or coincident with  $\overline{\text{CE}}$  LOW transition.



# Switching Waveforms (continued)

Figure 9. Write Cycle No. 1 (CE Controlled) [24, 25]

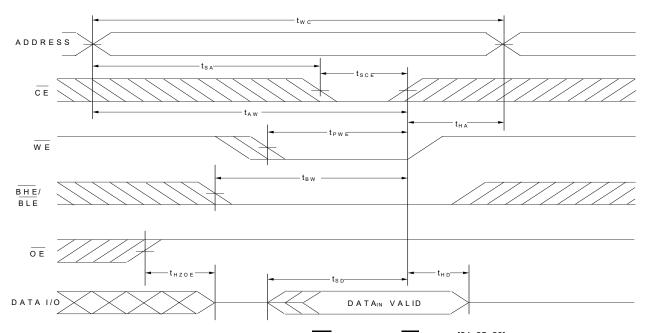
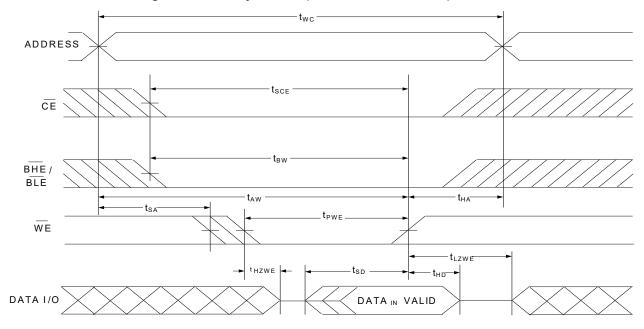


Figure 10. Write Cycle No. 2 (WE Controlled,  $\overline{\text{OE}}$  LOW)  $^{[24,\ 25,\ 26]}$ 



Notes

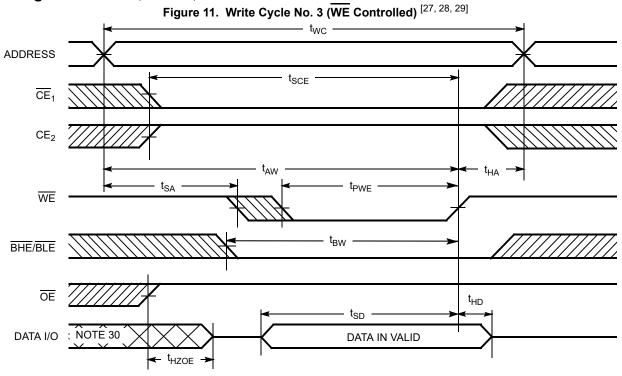
24. The internal write time of the memory is defined by the overlap of WE = V<sub>IL</sub>, \( \overlap \) = V<sub>IL</sub>. These signals must be LOW to initiate a write, and the HIGH transition of any of these signals can terminate the operation. The input data setup and hold timing should be referenced to the edge of the signal that terminates the write.

<sup>25.</sup> Data I/O is in HI-Z state if  $\overline{CE} = V_{IH}$ , or  $\overline{OE} = V_{IH}$ .

<sup>26.</sup> The minimum write cycle pulse width should be equal to sum of  $t_{SD}$  and  $t_{HZWE}$ .



# Switching Waveforms (continued)



<sup>27.</sup> The internal write time of the memory is defined by the overlap of WE = V<sub>IL</sub>, CE = V<sub>IL</sub>. These signals must be LOW to initiate a write, and the HIGH transition of any of these signals can terminate the operation. The input data setup and hold timing should be referenced to the edge of the signal that terminates the write.

28. Data I/O is nH-Z state if CE = V<sub>IH</sub>, or OE = V<sub>IH</sub>.

<sup>29.</sup> Data I/O is high impedance if  $\overrightarrow{OE} = V_{IH}$ .

30. During this period the I/Os are in output state. Do not apply input signals.



### **Truth Table**

CE	OE	WE	I/O <sub>0</sub> –I/O <sub>7</sub>	Mode	Power
Н	X <sup>[31]</sup>	X <sup>[31]</sup>	HI-Z	Power down	Standby (I <sub>SB</sub> )
L	L	Н	Data out	Read all bits	Active (I <sub>CC</sub> )
L	Х	L	Data in	Write all bits	Active (I <sub>CC</sub> )
L	Н	Н	HI-Z	Selected, outputs disabled	Active (I <sub>CC</sub> )

# **ERR Output - CY7C1049GE**

Output [32]	Mode	
0	Read operation, no single-bit error in the stored data.	
1	Read operation, single-bit error detected and corrected.	
HI-Z	Device deselected or outputs disabled or Write operation.	

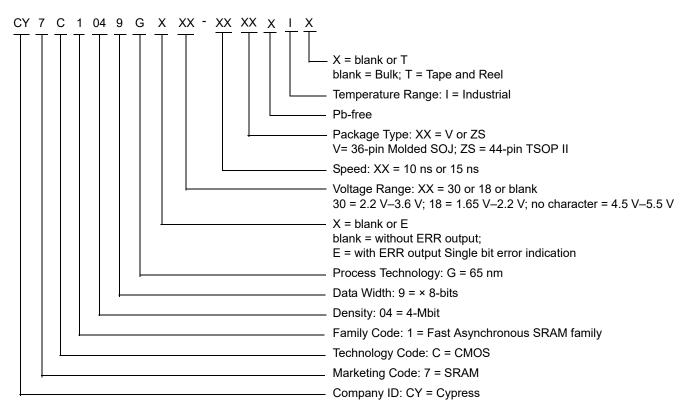
 $<sup>\</sup>label{eq:Notes} \textbf{31. The input voltage levels on these pins should be either at $V_{IH}$ or $V_{IL}$.} \\ \textbf{32. ERR pin is an output pin. It should be left floating when not used.}$ 



# **Ordering Information**

Speed (ns)	Voltage Range	Ordering Code	Package Diagram	Package Type (all Pb-free)	Operating Range
10	2.2 V-3.6 V	CY7C1049G30-10VXI	51-85090	36-pin Molded SOJ	Industrial
		CY7C1049G30-10VXIT	51-85090	36-pin Molded SOJ, Tape and Reel	
		CY7C1049GE30-10ZSXI	51-85087	44-pin TSOP II, ERR output	
		CY7C1049GE30-10ZSXIT	51-85087	44-pin TSOP II, ERR output, Tape and Reel	
		CY7C1049G30-10ZSXI	51-85087	44-pin TSOP II	
		CY7C1049G30-10ZSXIT	51-85087	44-pin TSOP II, Tape and Reel	
15	1.65 V-2.2 V	CY7C1049G18-15ZSXI	51-85087	44-pin TSOP II	
		CY7C1049G18-15ZSXIT	51-85087	44-pin TSOP II, Tape and Reel	
10	4.5 V-5.5 V	CY7C1049G-10VXI	51-85090	36-pin Molded SOJ	
		CY7C1049G-10VXIT	51-85090	36-pin Molded SOJ, Tape and Reel	
		CY7C1049G-10ZSXI	51-85087	44-pin TSOP II	
		CY7C1049G-10ZSXIT	51-85087	44-pin TSOP II, Tape and Reel	

### **Ordering Code Definitions**





# **Package Diagrams**

Figure 12. 44-pin TSOP II Package Outline, 51-85087

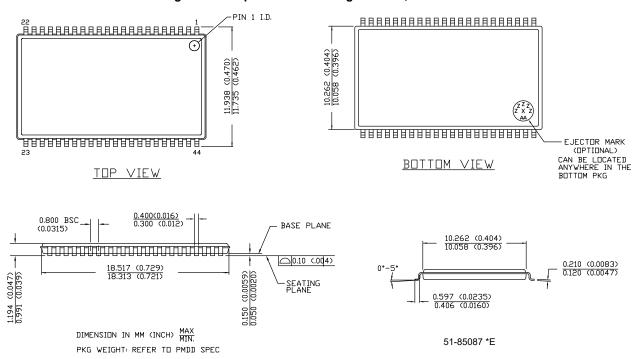
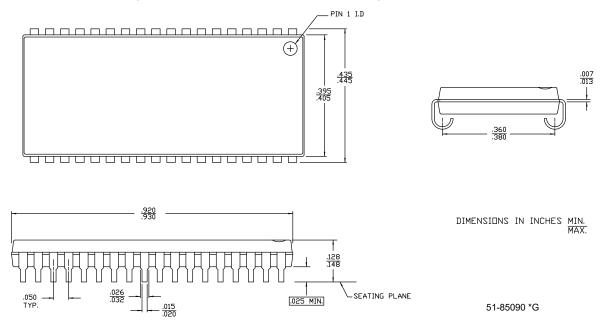


Figure 13. 36-pin SOJ V36.4 (Molded) Package Outline, 51-85090





# **Acronyms**

Acronym	Description			
BHE	Byte High Enable			
BLE	Byte Low Enable			
CE	Chip Enable			
CMOS	Complementary Metal Oxide Semiconductor			
I/O	Input/Output			
ŌĒ	Output Enable			
SRAM	Static Random Access Memory			
TSOP	Thin Small Outline Package			
TTL	Transistor-Transistor Logic			
VFBGA	Very Fine-Pitch Ball Grid Array			
WE	Write Enable			

# **Document Conventions**

### **Units of Measure**

Symbol	Unit of Measure		
°C	degrees Celsius		
MHz	megahertz		
μΑ	microampere		
μS	microsecond		
mA	milliampere		
mm	millimeter		
ns	nanosecond		
Ω	ohm		
%	percent		
pF	picofarad		
V	volt		
W	watt		



# **Document History Page**

Rev.	ECN No.	Orig. of Change	Submission Date	Description of Change	
**	4685774	VINI	03/13/2015	New data sheet.	
*A	4831087	NILE	07/10/2015	Updated Package Diagrams: Added spec 51-85090 *G (Figure 13). Removed spec 51-85082 *E. Removed spec 51-85150 *H.	
*B	4968879	NILE	10/16/2015	Fixed typo in bookmarks.	
*C	5020573	VINI	11/25/2015	Changed status from Preliminary to Final. Updated Pin Configurations: Removed figure "36-pin SOJ Single Chip Enable with ERR CY7C10490 Updated Ordering Information: Updated part numbers.	
*D	5429076	NILE	09/07/2016	Updated Maximum Ratings: Updated Note 8 (Replaced "2 ns" with "20 ns"). Updated DC Electrical Characteristics: Removed Operating Range "2.7 V to 3.6 V" and all values corresponding to V <sub>OH</sub> parameter. Included Operating Ranges "2.7 V to 3.0 V" and "3.0 V to 3.6 V" and all values corresponding to V <sub>OH</sub> parameter. Changed minimum value of V <sub>IH</sub> parameter from 2.2 V to 2 V corresponding to Operating Range "4.5 V to 5.5 V". Updated Ordering Information: Updated part numbers. Updated to new template.	
*E	5725349	AESATMP7	05/03/2017	Updated Cypress Logo and Copyright.	
*F	6118848	NILE	04/03/2018	Updated Features: Added Note 2 and referred the same note in "Embedded ECC for single-bit error correction". Updated to new template. Completing Sunset Review.	



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